WHAT IS CLAIMED IS

1. A capacitor, comprising:

a capacitor part comprising a dielectric film sandwiched by a pair of electrodes; and

a support body of a film of an organic polysilane, said support body supporting said capacitor part thereon.

2. The capacitor as claimed in claim 1, further comprising an insulation layer covering said capacitor part.

3. A method of manufacturing a capacitor including a capacitor part in which a dielectric film is sandwiched by a pair of electrodes and a support body of an organic polysilane film supporting said capacitor part, comprising the steps of:

forming a layer of organic polysilane on a surface of a base material;

forming a first electrode on said layer of organic polysilane;

forming a dielectric film on said first electrode;

forming a second electrode on said dielectric film;

forming an insulation layer on said layer of organic polysilane and on said second electrode;

said layer of organic polysilane, said first electrode, said dielectric film, said second electrode and said insulation layer forming a layered body on said base material,

forming a groove in said layer of organic silane and said insulation layer for dividing said layered body into individual capacitors; and

removing said base material.

4. The method as claimed in claim 3, wherein said step of removing said base material is conducted in the state that a tape is attached to a top surface of said insulation layer so as to bridge said groove.

5. substrate for mounting a semiconductor chip thereon, comprising:

a substrate body defined by upper and bottom surfaces;

a plurality of terminals provided on said top surface for connection with a semiconductor chip mounted on said top surface, said top surface thereby forming a chip-mounting surface;

a plurality of terminals provided on said

bottom surface for external connection, said bottom surface thereby forming a mounting surface; and

a capacitor embedded in said substrate body right underneath said chip-mounting surface,

said capacitor comprising:

a capacitor part including a dielectric film sandwiched by a pair of electrodes; and

a support body of an organic polysilane film supporting said capacitor part.

6. A method of manufacturing a substrate for mounting a semiconductor chip, said substrate having a mounting surface carrying thereon terminals for external connection at a lower principal surface and a chip-mounting surface for carrying a semiconductor chip at an upper principal surface, said substrate further including a capacitor embedded right underneath said chip-mounting surface such that said capacitor includes a capacitor part formed of a dielectric film sandwiched by a pair of electrodes and a support body of an organic polysilane film supporting said capacitor part, said capacitor having an insulation film covering said capacitor part,

said method comprising the steps of:

bonding said capacitor on a base;

forming an insulation layer on said base such that said insulation layer covers said capacitor;

laminating a plurality of insulation layers on said base so as to cover said capacitor; and

removing said base.

7. A semiconductor device, comprising:

a substrate; and

a semiconductor chip mounted on said substrate,

said substrate comprising:

a substrate body defined by upper and bottom surfaces;

a plurality of terminals provided on said top surface for connection with said semiconductor chip mounted on said top surface, said top surface thereby forming a chip-mounting surface;

a plurality of terminals provided on said bottom surface for external connection, said bottom surface thereby forming a mounting surface; and

a capacitor embedded in said substrate body right underneath said chip-mounting surface,

said capacitor comprising:

a capacitor part including a dielectric film sandwiched by a pair of electrodes; and

a support body of an organic polysilane film supporting said capacitor part.